







SN74LV10A SCES338G - SEPTEMBER 2000 - REVISED MARCH 2023

# **SN74LV10A Triple 3-Input Positive-NAND Gate**

#### 1 Features

- V<sub>CC</sub> operation of 2 V to 5.5 V
- Max t<sub>pd</sub> of 7 ns at 5 V
- Typical V<sub>OLP</sub> (Output Ground Bounce) <0.8 V at  $V_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) >2.3 V at  $V_{CC} = 3.3 \text{ V}, \text{ TA} = 25^{\circ}\text{C}$
- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

## 2 Applications

- Alarm / tamper detect circuit
- S-R latch

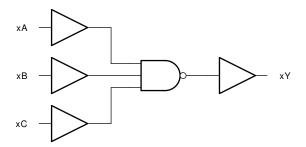
## 3 Description

These triple 3-input positive-NAND designed for 2 V to 5.5 V V<sub>CC</sub> operation. The SN74LV10A devices perform the Boolean function Y = A • B • C in positive logic. These devices are fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

# Package Information<sup>(1)</sup>

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)	
	D (SOIC, 14)	8.65 mm x 3.90 mm	
SN74LV10A	NS (SO, 14)	10.20 mm x 5.30 mm	
	PW (TSSOP, 14)	5.00 mm x 4.40 mm	

For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Schematic



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NOTE: Page numbers for previous revisions may differ f	om page numbers in the current version.	

# Changes from Revision F (May 2022) to Revision G (March 2023) Page Updated the structural layout of document to current standard, added Applications section, and updated Package Information table......1 Changes from Revision E (April 2015) to Revision F (May 2022) Page

Updated the numbering, formatting, tables, figures and cross-references throughout the document to reflect modern data sheet standards......1



# **5 Pin Configuration and Functions**

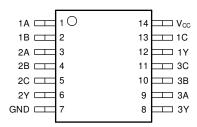


Figure 5-1. SN74LV10A . . . D, NS, or PW Package (Top View)

Table 5-1. Pin Functions

	PIN	TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.	- ITPE(")	DESCRIPTION
1A	1	I	1A Input
1B	2	I	1B Input
NC	3	_	Not internally connected
1C	4	I	1C Input
1D	5	I	1D Input
1Y	6	0	1Y Output
2Y	8	0	2Y Output
2A	9	I	2A Input
2B	10	I	2B Input
NC	11	_	Not internally connected
2C	12	I	2C Input
2D	13	I	2D Input
GND	7	_	Ground Pin
V <sub>CC</sub>	14	_	Power Pin

<sup>(1)</sup> Signal Types: I = Input, O = Output.



# **6 Specifications**

# **6.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

	<u> </u>	·	MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>	Input voltage range <sup>(2)</sup>		7	V
Vo	Output voltage range applied	Output voltage range applied in high or low state <sup>(2) (3)</sup>			V
Vo	Output voltage range applied	Output voltage range applied in power-off state <sup>(2)</sup>			
I <sub>IK</sub>	Input clamp current	(V <sub>I</sub> < 0)		-20	mA
I <sub>OK</sub>	Output clamp current	(V <sub>O</sub> < 0)		-50	mA
Io	Continuous output current	(V <sub>O</sub> = 0 to V <sub>CC</sub> )		±25	mA
	Continuous current through V	CC or GND		±50	mA
$\theta_{JA}$	Package thermal impedance			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	± 2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Machine Model, per JEDEC specification	± 200	V
		Charged device model (CDM), per JEDEC specification JS-002 (2)	± 1000	

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

# **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2	5.5	V
		V <sub>CC</sub> = 2 V	1.5		
.,	High level in motor life me	V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.7		V
$V_{IH}$	High level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.7		V
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.7		
		V <sub>CC</sub> = 2 V		0.5	
	Lavolaval innut valtana	V <sub>CC</sub> = 2.3 V to 2.7 V		V <sub>CC</sub> × 0.3	V
$V_{IL}$	Low level input voltage	V <sub>CC</sub> = 3 V to 3.6 V		V <sub>CC</sub> × 0.3	V
		V <sub>CC</sub> = 4.5 V to 5.5 V		V <sub>CC</sub> × 0.3	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 2 V		-50	μA
	High level autout august	V <sub>CC</sub> = 2.3 V to 2.7 V		-2	
I <sub>OH</sub>	High level output current	V <sub>CC</sub> = 3 V to 3.6 V		-6	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V		-12	

Product Folder Links: SN74LV10A

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(3)</sup> This value is limited to 5.5 V maximum.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

# 6.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN MAX	UNIT
		V <sub>CC</sub> = 2 V	50	μА
	Low lovel output ourrent	V <sub>CC</sub> = 2.3 V to 2.7 V	2	
I <sub>OL</sub>	Low level output current	V <sub>CC</sub> = 3 V to 3.6 V	6	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V	12	
		V <sub>CC</sub> = 2.3 V to 2.7 V	200	
Δt/Δν	Input transition rise and fall rate	V <sub>CC</sub> = 3 V to 3.6 V	100	ns/V
		V <sub>CC</sub> = 4.5 V to 5.5 V	20	
T <sub>A</sub>	Operating free-air temperature	•	<b>-40</b> 85	°C

<sup>(1)</sup> All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004

#### **6.4 Thermal Information**

			SN74LV10A		
	THERMAL METRIC <sup>(1)</sup>	D	NS	PW	UNIT
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86	76	113	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report (SPRA953).

#### 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP	MAX	UNIT	
		I <sub>OH</sub> = -50 μA	2 V to 5.5 V	V <sub>CC</sub> - 0.1				
V <sub>OH</sub>	OH High-level output voltage	I <sub>OH</sub> = -2 mA	2.3 V	2			V	
VOH	nigh-level output voltage	I <sub>OH</sub> = -6 mA	3 V	2.48			V	
		I <sub>OH</sub> = -12 mA	4.5 V	3.8				
		I <sub>OL</sub> = 50 μA	2 V to 5.5 V			0.1		
	Levelevel entent veltere	I <sub>OL</sub> = 2 mA	2.3 V			0.4	v	
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 6 mA	3 V			0.44	V	
		I <sub>OL</sub> = 12 mA	4.5 V			0.55		
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±1	μA	
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> I <sub>O</sub> = 0	5.5 V			20	μА	
C <sub>i</sub>	Input capacitance	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		1.9		pF	

# 6.6 Switching Characteristics, $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	то	LOAD	1	T <sub>A</sub> = 25°C		SN74LV	10A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	UNIT
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 15 pF		7.1	13	1	15.5	ns
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 50 pF		10.3	17.1	1	20.5	115

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# 6.7 Switching Characteristics, $V_{CC}$ = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (seeFigure 7-1)

PARAMETER	FROM	то	LOAD	Т	A = 25°C		SN74LV	10A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	UNII
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 15 pF		5.2	8.4	1	10	no
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 50 pF		7.4	11.9	1	13.5	ns

# 6.8 Switching Characteristics, $V_{CC}$ = 5 V $\pm$ 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 7-1)

PARAMETER	FROM	то	LOAD	1	Γ <sub>A</sub> = 25°C		SN74L\	/10A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	UNII
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 15 pF		3.9	5.9	1	7	ne
t <sub>pd</sub>	A, B, or C	Y	C <sub>L</sub> = 50 pF		5.4	7.9	1	9	ns

### **6.9 Noise Characteristics**

 $V_{CC}$  = 3.3 V,  $C_{L}$  = 50 pF,  $T_{A}$  = 25°C

	PARAMETER <sup>(1)</sup>	MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.2	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>OL</sub>		0	-0.8	V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>		3.2		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.31			V
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.99	V

(1) Characteristics are for surface-mount packages only.

# **6.10 Operating Characteristics**

 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST C	CONDITIONS	V <sub>cc</sub>	TYP	UNIT
	Power dissipation capacitance	$C_1 = 50 \text{ pF},$	f = 10 MHz	3.3 V	14	nE
Opd	rower dissipation capacitance	$C_L = 50 \text{ pF},$	1 - 10 WITZ	5 V	16.7	p⊦

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### 7 Parameter Measurement Information

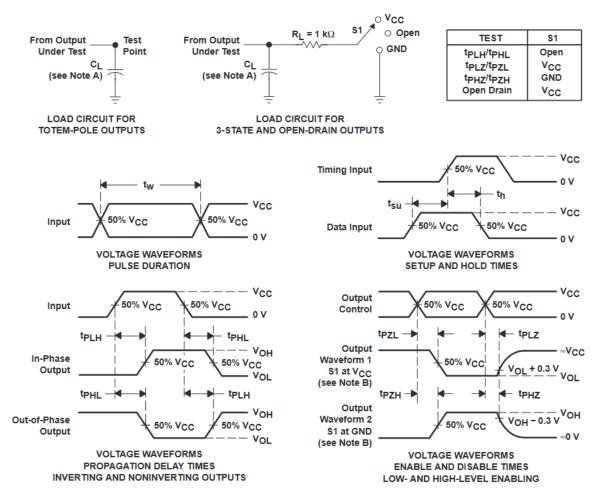


Figure 7-1. Load Circuit and Voltage Waveforms

- A. C<sub>L</sub> includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq$  3 ns.  $t_f \leq$  3 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as t<sub>dis</sub>.
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

# **8 Detailed Description**

### 8.1 Overview

These triple 3-input positive-NAND gates are designed for 2-V to 5.5-V  $V_{CC}$  operation. The SN74LV10A devices perform the Boolean function  $Y = \overline{A \cdot B \cdot C}$  in positive logic. These devices are fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

## 8.2 Functional Block Diagram

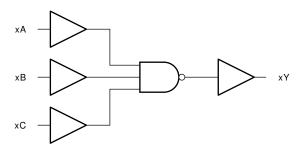


Figure 8-1. Simplified Schematic

#### 8.3 Device Functional Modes

Table 8-1. FUNCTION TABLE (each gate)

II	OUTPUT (2)		
Α	В	С	Y
Н	Н	Н	L
L	Χ	Χ	Н
X	L	Χ	Н
×	Χ	L	Н

- (1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
- (2) H = Driving High, L = Driving Low

# 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

#### 9.2 Layout

#### 9.2.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V<sub>CC</sub>, whichever makes more sense for the logic function or is more convenient.

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# 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **10.1 Documentation Support**

#### 10.1.1 Related Documentation

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 10-1. Related Links

PARTS PRODUCT FOLDER		SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74LV10A	Click here	Click here	Click here	Click here	Click here

## 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 10.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: SN74I V10A

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV10AD	LIFEBUY	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	
SN74LV10ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples
SN74LV10ADRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples
SN74LV10ANSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	74LV10A	Samples
SN74LV10APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples
SN74LV10APWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



# **PACKAGE OPTION ADDENDUM**

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV10ADR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74LV10ANSR	so	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74LV10APWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV10ADR	SOIC	D	14	2500	356.0	356.0	35.0
SN74LV10ANSR	SO	NS	14	2000	356.0	356.0	35.0
SN74LV10APWR	TSSOP	PW	14	2000	356.0	356.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74LV10AD	D	SOIC	14	50	506.6	8	3940	4.32

# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



# D (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
  - Sody length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



# **MECHANICAL DATA**

# NS (R-PDSO-G\*\*)

# 14-PINS SHOWN

### PLASTIC SMALL-OUTLINE PACKAGE



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- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



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